



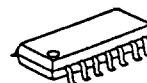
GaAs POWER AMPLIFIER IC

■ GENERAL DESCRIPTION

NJG1304E is a GaAs MMIC designed mainly for driver amplifier of PHS base station in Japan.

This is a variable gain type with 20dB dynamic range. It features very low distortion and P_{acp} is less than -70dBc at 17 dBm output power, and enables low voltage and high efficiency operation.

Small Plastic mold Package are adopted.

■ PACKAGE OUTLINE


NJG1304E

■ APPLICATIONS

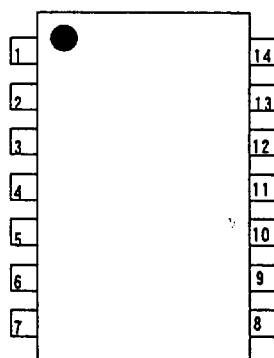
- PHS base station etc.

■ FEATURES

- Variable gain under low distortion
- Low voltage operation ($V_{DD}=3.0V$)
- Input and output internal matching circuits
- High gain (32dB Typ.)
- Low distortion ($P_{acp}=-70dBc$ Typ.@1.9GHz,17dBm)
- Low current consumption ($I_{DD}=180mA$ Typ.@1.9GHz,17dBm)
- Reduction of Parasitic oscillation
- EMP 14 Maximum Power Dissipation: 1000mW($T_j=150^{\circ}C$,PCB: 24*30*1.0mm FR4)

■ PIN CONFIGURATION

(Top View)



Pin Connection

1.GND	8.GND
2.RF _{in}	9.RF _{out}
3.V _{GG1}	10.V _{DD2}
4.V _{cont}	11.GND
5.V _{GG2}	12.V _{DD1}
6.GND	13.GND
7.GND	14.GND


■ ABSOLUTE MAXIMUM RATINGS
 $(Z_s=Z_o=50\text{ohm}, T_a=25^\circ\text{C})$

PARAMETER	SYMBOL	CONDITIONS	RATINGS	UNIT
Drain Voltage	V_{DD1}, V_{DD2}	$V_{GG1,2}=-0.9\text{V}$	6	V
Gate Voltage	V_{GG1}, V_{GG2}	$V_{DD1,2}=3.0\text{V}$	-4	V
Gain control voltage	V_{cont}	$V_{DD1,2}=3.0\text{V}$	-4	V
Input Power	P_{in}	$V_{DD1,2}=3.0\text{V}, V_{GG1,2}=-0.9\text{V}$	3	dBm
Power Dissipation	P_D	24*30*1.0mm PCB : FR4, $T_J=150^\circ\text{C}$	1000	mW
Operating Temperature	T_{opr}		-30~+85	$^\circ\text{C}$
Storage Temperature	T_{stg}		-40~+150	$^\circ\text{C}$

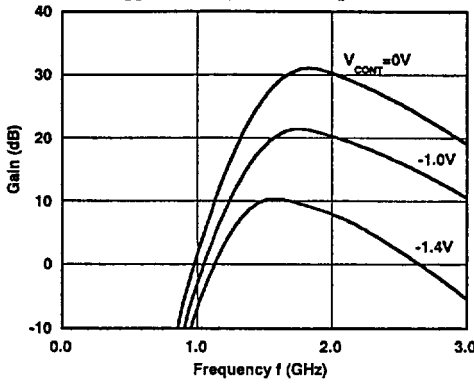
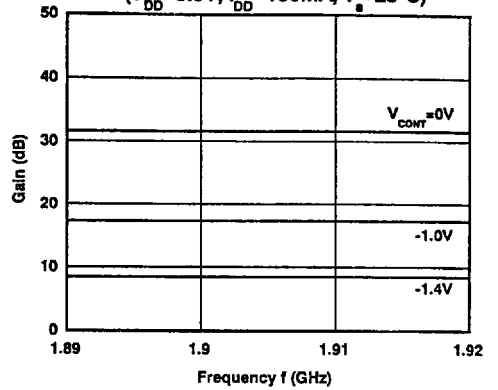
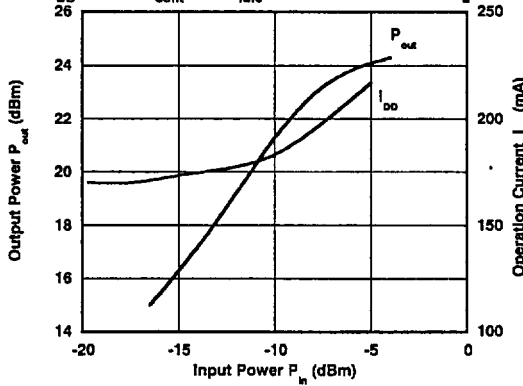
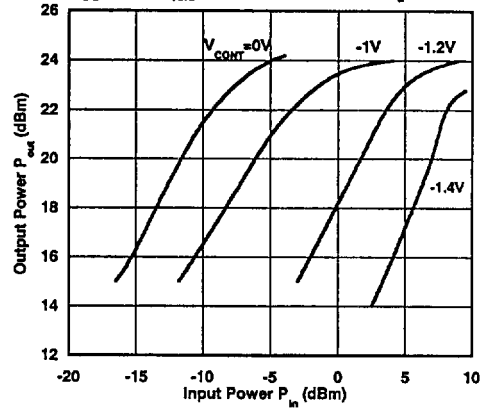
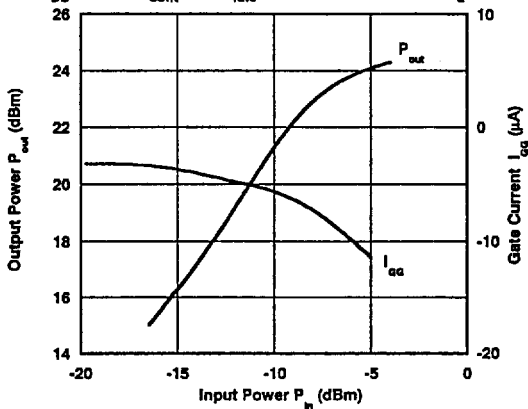
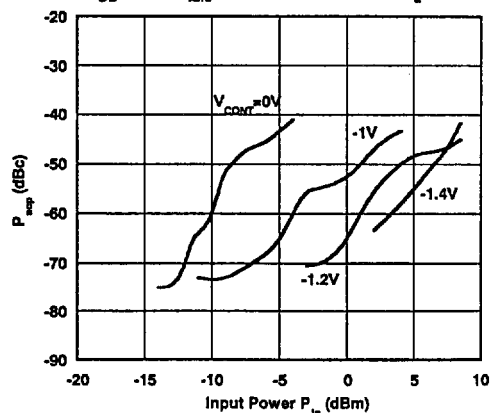
■ ELECTRICAL CHARACTERISTICS
 $(f=1.9\text{GHz}, Z_s=Z_o=50\text{ohm}, T_a=25^\circ\text{C})$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Operating Frequency	freq	$V_{DD1,2}=3.0\text{V}$	1.89	-	1.92	GHz
Drain Voltage	$V_{DD1,2}$		2.9	3.0	5.3	V
Gate Voltage	$V_{GG1,2}$	$V_{DD1,2}=3.0\text{V}, I_{idle}=180\text{mA}$	-1.25	-0.9	-0.6	V
Idle Current *1	I_{idle}	$V_{DD1,2}=3.0\text{V}$, No RF Signal	175	180	185	mA
Operating Current *1	I_{DD}	$P_{out}=17\text{dBm}, V_{DD1,2}=3.0\text{V}$	170	180	190	mA
Gate Current *2	I_{GG}	$P_{out}=17\text{dBm}, V_{DD1,2}=3.0\text{V}$	-150	-70	-	μA
Gain Control Terminal Current	I_{cont}	$P_{out}=17\text{dBm}, V_{DD1,2}=3.0\text{V}$ $-2.0\text{V} < V_{cont} < 0.0\text{V}$	-5	-2	-	μA
Gain Control Voltage			-2.0	-	0	V
Small Signal Gain	Gain	$V_{DD1,2}=3.0\text{V}, I_{idle}=180\text{mA}$	29	32	35	dB
Gain Flatness	G_{flat}	$V_{DD1,2}=3.0\text{V}, I_{idle}=180\text{mA}$	0.0	0.5	1.0	dB
Gain Control Range	G_{cont}	$V_{cont}=2\sim 0\text{V}, V_{DD1,2}=3.0\text{V}$ $I_{idle}=180\text{mA}$	18	20	23	dB
Pout at 1dB Compression	P_{-1dB}	$V_{DD1,2}=3.0\text{V}$	22	23	-	dBm
Adjacent Channel Leakage Power ①	P_{acp1}	$P_{out}=17\text{dBm}, \text{offset}=600\text{kHz}$, $P_{in}; \pi/4 \text{ QPSK}, V_{DD1,2}=3.0\text{V}$	-	-	-70	dBc
Adjacent Channel Leakage Power ②	P_{acp2}	$P_{out}=17\text{dBm}, \text{offset}=900\text{kHz}$, $P_{in}; \pi/4 \text{ QPSK}, V_{DD1,2}=3.0\text{V}$	-	-	-70	dBc
Adjacent Channel Leakage Power ③	P_{acp3}	$P_{in}=-7\text{dBm}, \text{offset}=600\text{kHz}$ $P_{out}=13\text{dBm}$ (Adjust V_{cont}) $P_{in}; \pi/4 \text{ QPSK}, V_{DD1,2}=3.0\text{V}$	-	-	-70	dBc
Adjacent Channel Leakage Power ④	P_{acp4}	$P_{in}=-7\text{dBm}, \text{offset}=900\text{kHz}$ $P_{out}=13\text{dBm}$ (Adjust V_{cont}) $P_{in}; \pi/4 \text{ QPSK}, V_{DD1,2}=3.0\text{V}$	-	-	-70	dBc
Harmonics	P_{sp}	$P_{in}; \pi/4 \text{ QPSK}, V_{DD1,2}=3.0\text{V}$	-	-35	-30	dBc
Input VSWR	VSWR _i	$P_{out}=21\text{dBm}, V_{DD1,2}=3.0\text{V}$ $V_{DD1,2}=3.0\text{V}$	-	-	2.2	
Load VSWR Tolerance		$P_{out}=21\text{dBm}, V_{DD1,2}=3.0\text{V}$ Load VSWR=4:1, All Phase				

 Parasitic Oscillation for
 Fundamental Signal Level
 : $\leq -60\text{dBc}$

 *1 ; V_{DD1} Terminal and V_{DD2} Terminal Total Current

 *2 ; V_{GG1} Terminal and V_{GG2} Terminal Total Current

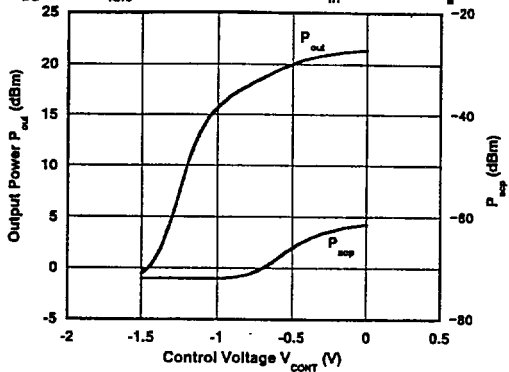

■ TYPICAL CHARACTERISTICS
Gain vs. Frequency vs. Control Voltage
 $(V_{DD}=3.0V, I_{DD}=180mA, T_a=25^\circ C)$

Gain vs PHS Band Frequency vs. Control Voltage
 $(V_{DD}=3.0V, I_{DD}=180mA, T_a=25^\circ C)$

Output Power, Operating Current vs. Input Power
 $(V_{DD}=3.0V, V_{CONT}=0V, I_{idle}=180mA, f=1.9GHz, T_a=25^\circ C)$

Output Power vs. Input Power vs. Control Voltage
 $(V_{DD}=3.0V, I_{idle}=180mA, f=1.9GHz, T_a=25^\circ C)$

Output Power, Gate Current vs. Input Power
 $(V_{DD}=3.0V, V_{CONT}=0V, I_{idle}=180mA, f=1.9GHz, T_a=25^\circ C)$

 P_{acp} vs. Input Power vs. Control Voltage
 $(V_{DD}=3.0V, I_{idle}=180mA, f=1.9GHz, T_a=25^\circ C)$




■ TYPICAL CHARACTERISTICS

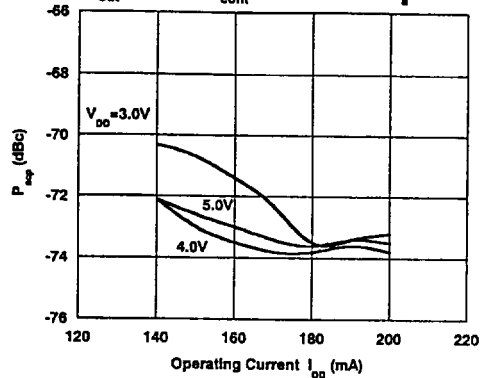
Output Power, P_{acp} vs. Control Voltage

($V_{DD}=3.0V, I_{idle}=180mA, f=1.9GHz, P_{in}=-11dBm, T_a=25^\circ C$)



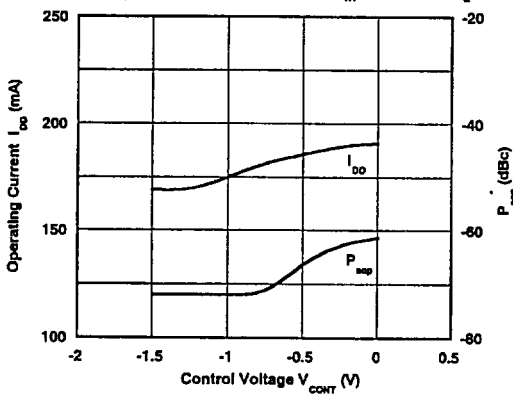
P_{acp} vs. Operating Current vs. V_{DD}

($P_{out}=17dBm, V_{cont}=0V, f=1.9GHz, T_a=25^\circ C$)



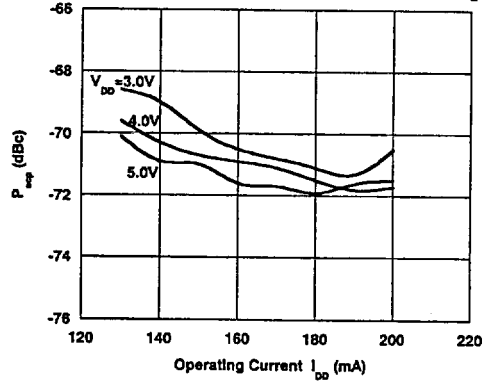
Operating Current, P_{acp} vs. Control Voltage

($V_{DD}=3.0V, I_{idle}=180mA, f=1.9GHz, P_{in}=-11dBm, T_a=25^\circ C$)



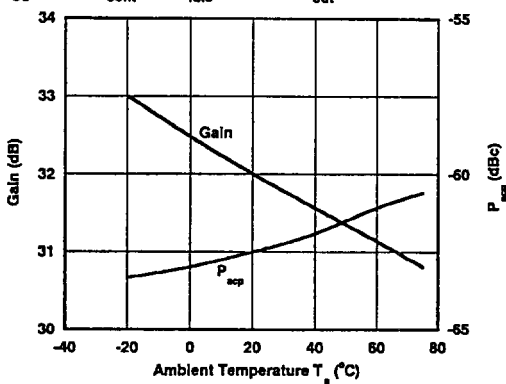
P_{acp} vs. Operating Current vs. V_{DD}

($P_{out}=13dBm, P_{in}=-7dBm, V_{cont}=-1.1V, f=1.9GHz, T_a=25^\circ C$)



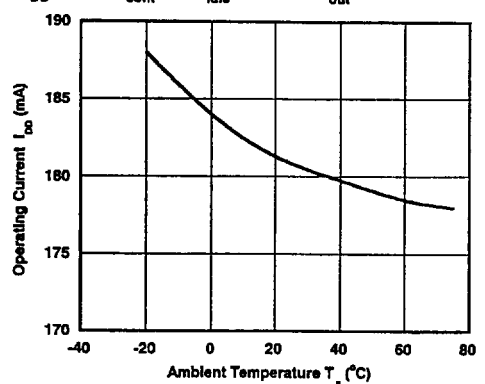
Gain, P_{acp} vs. Ambient Temperature

($V_{DD}=3.0V, V_{cont}=0V, I_{idle}=180mA, P_{out}=21dBm, f=1.9GHz$)



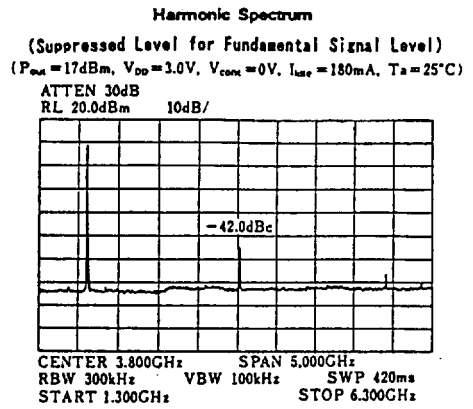
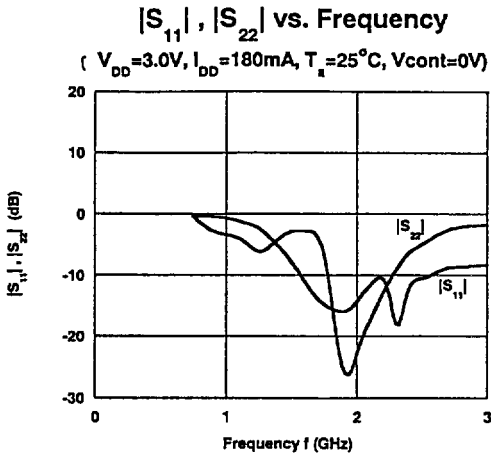
Operating Current vs. Ambient Temperature

($V_{DD}=3.0V, V_{cont}=0V, I_{idle}=180mA, P_{out}=21dBm, f=1.9GHz$)





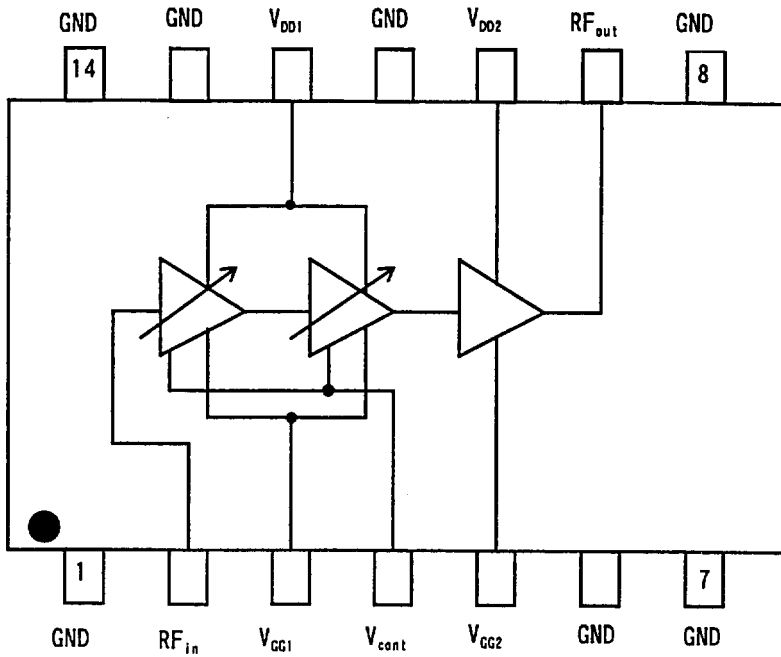
TYPICAL CHARACTERISTICS



All adjacent channel leakage power used in these characteristics are those of 600KHz offset for fundamental wave at PHS operating condition($\pi/4$ QPSK)

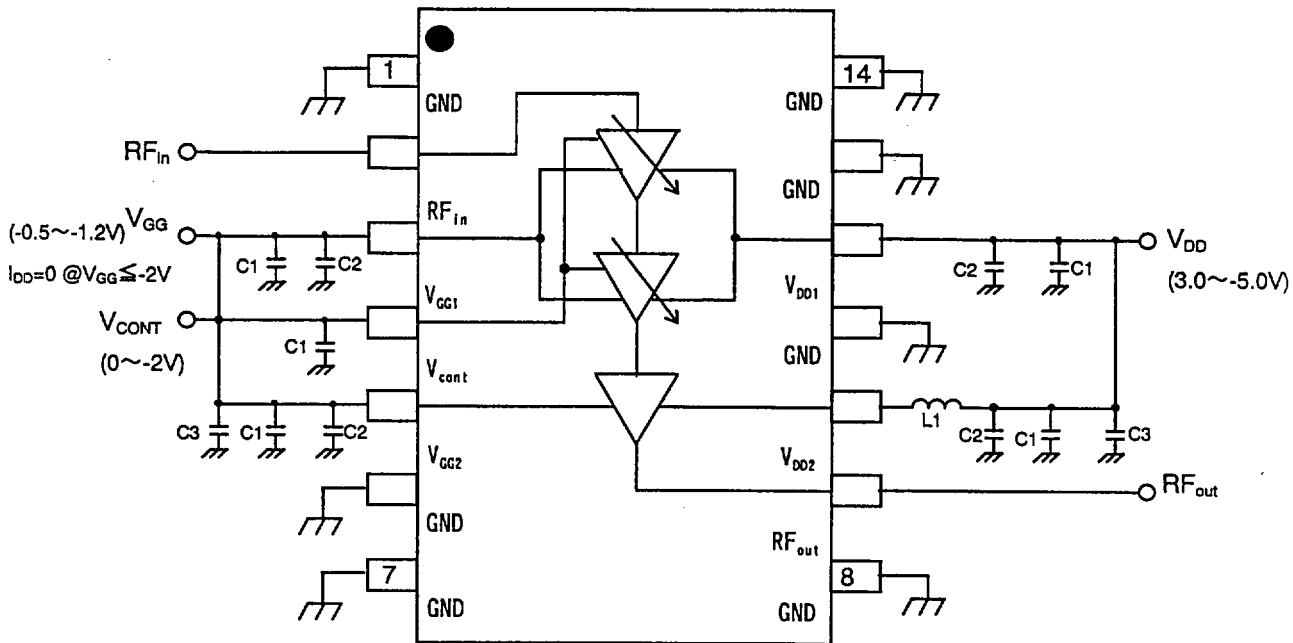


■ BLOCK DIAGRAM





RECOMMENDED CIRCUIT



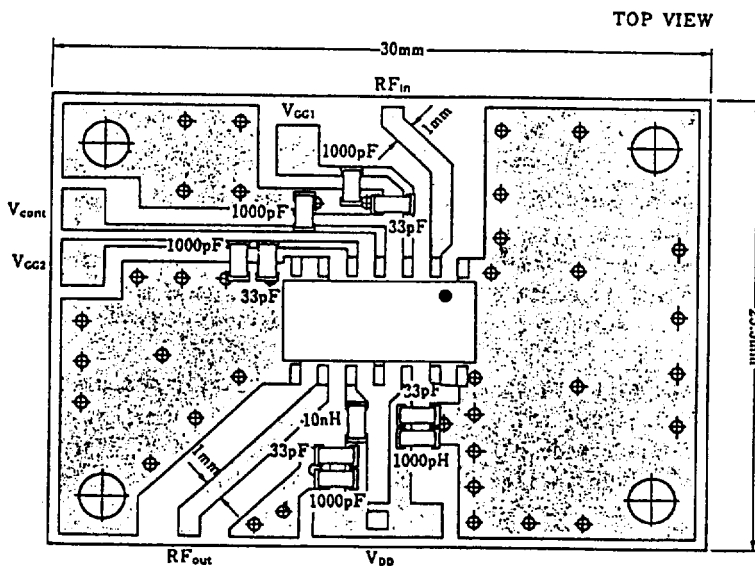
C1:1000pF

C2:33pF

C3:1 μ F

C4:10nH

RECOMMENDED PCB

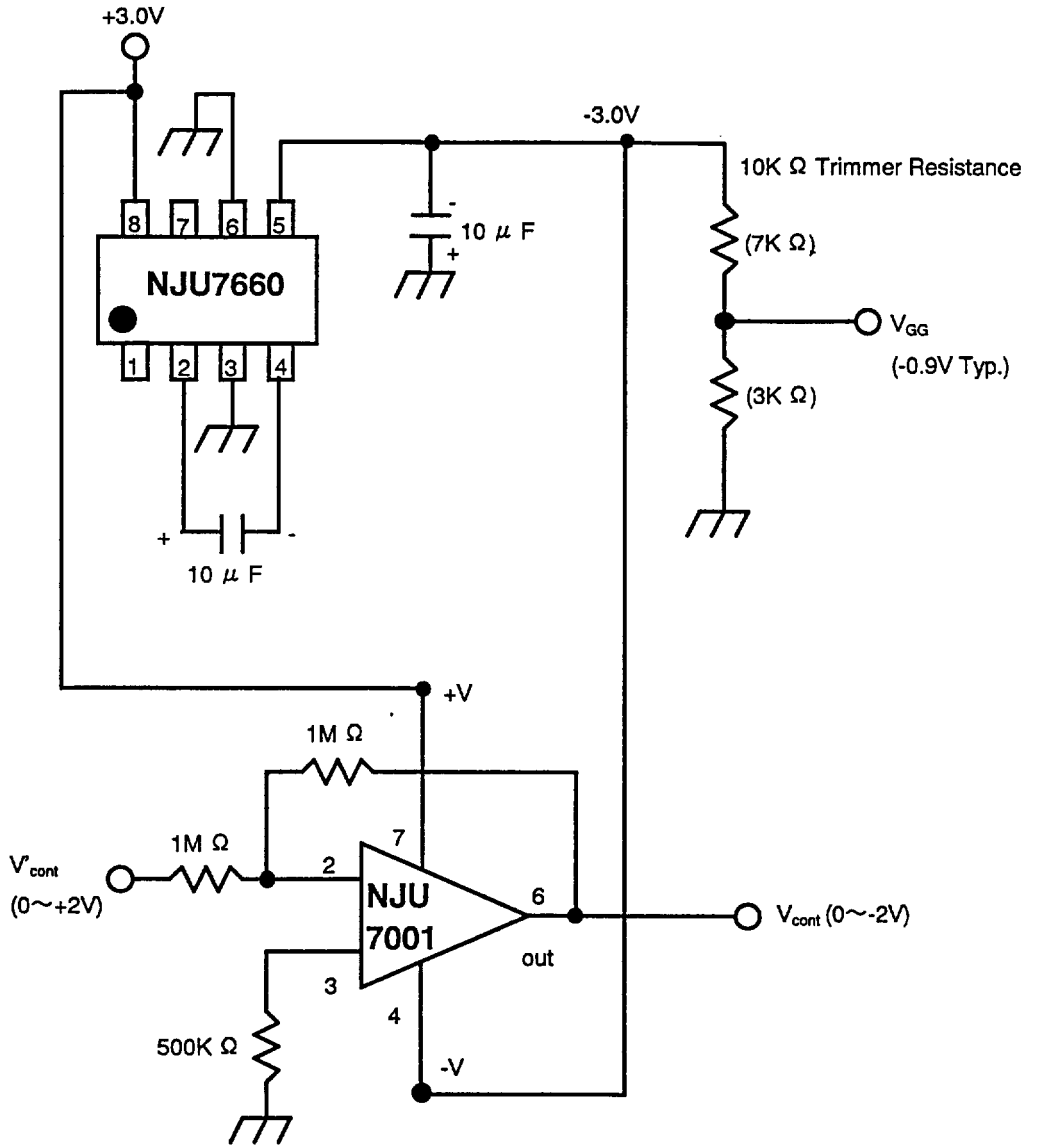


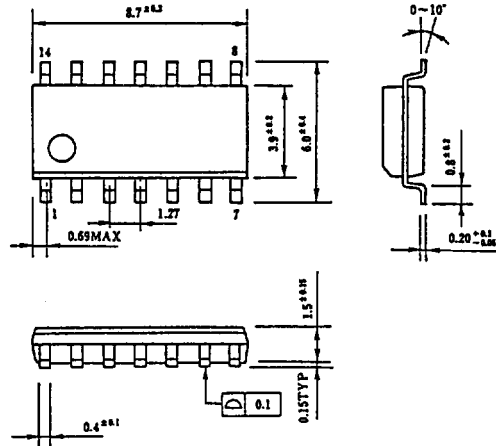
PCB : FR4, t=0.5mm
 CAPACITOR :
 MURATA GRM39Series
 INDUCTOR :
 TAIYO YUDEN HK2125Series

The reflow method is recommended to install this device to PCB.



RECOMMENDED PCB




PACKAGE OUTLINE
EMP14


UNIT: mm

Caution on using the products

A GaAs is used in this product. A GaAs is a harmful material.

- Don't eat or in the mouth.
- Don't dispose in fire or break up the products.
- Don't make a gas or a powdered with the chemical reaction.
- In the case of wasting the products, please obey the relation rule in the each country.

This product may be broken with static electric discharge or serge voltage. Therefore, please note a handling.

The other caution item

- The product specifications and descriptions listed in this catalog are subject to change at any time, without notice.
- We don't take upon ourselves the responsibilities that infringe on other people's rights of a patents bringing about the information and drawing in this catalog.
- It is not purpose to be equipped with the system needs a high reliability as air system, submarine cable system, atomic energy control system and medical instrument for keeping life.
- If you think the above system, please ask for the sales office before.